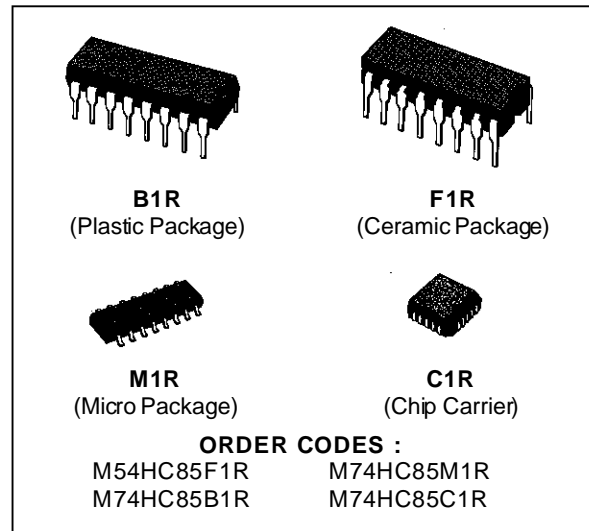


4-BIT MAGNITUDE COMPARATOR

- HIGH SPEED
 $t_{PD} = 22 \text{ ns}$ (TYP.) at $V_{CC} = 5 \text{ V}$
- LOW POWER DISSIPATION
 $I_{CC} = 4 \mu\text{A}$ (MAX.) at $T_A = 25 \text{ }^\circ\text{C}$
- HIGH NOISE IMMUNITY
 $V_{NIH} = V_{NIL} = 28 \% V_{CC}$ (MIN.)
- OUTPUT DRIVE CAPABILITY
 10 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
 $|I_{OH}| = I_{OL} = 4 \text{ mA}$ (MIN.)
- BALANCED PROPAGATION DELAYS
 $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
 V_{CC} (OPR) = 2 V to 6 V
- PIN AND FUNCTION COMPATIBLE WITH
 54/74LS85



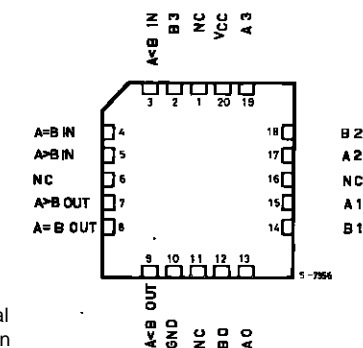
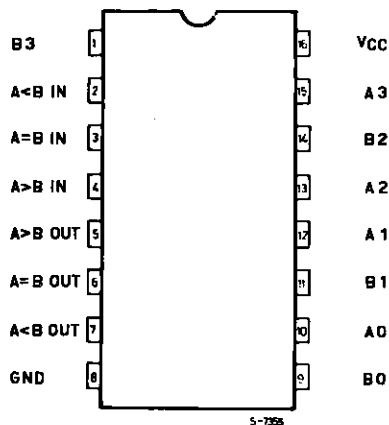
DESCRIPTION

The M54/74HC85 is a high speed CMOS 4-BIT MAGNITUDE COMPARATOR fabricated in silicon gate C²MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. This comparator compares two 4-bit words and provides a high voltage level on one of the A > B out, A = B out and A < B out outputs. The comparing bit number is easily expanded by cascading several devices as shown in the typical application. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN CONNECTIONS (top view)

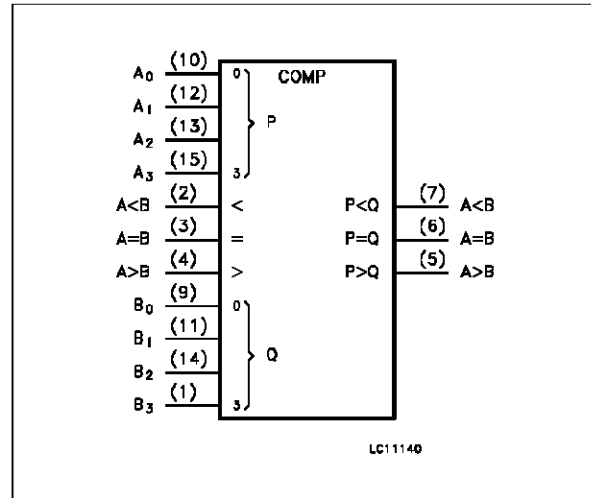


M54/M74HC85

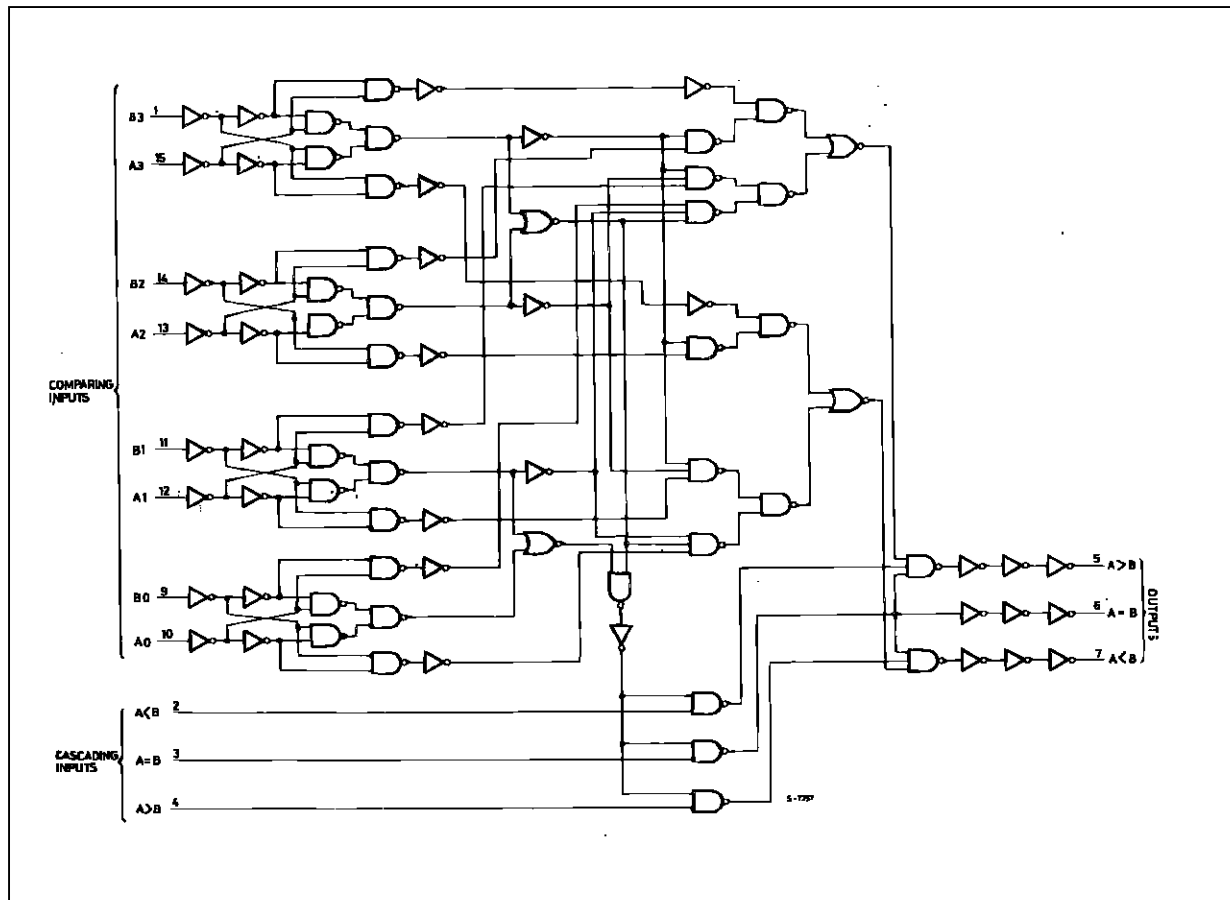
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
2	IN _{A<B}	A<B Expansion Input
3	IN _{A=B}	A=B Expansion Input
4	IN _{A>B}	A>B Expansion Input
5	OUT _{A>B}	A>B Expansion Output
6	OUT _{A=B}	A=B Expansion Output
7	OUT _{A<B}	A<B Expansion Output
9, 11, 14, 1	B ₀ to B ₃	Word B Inputs
10, 12, 13, 15	A ₀ to A ₃	Word A Inputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



LOCIG DIAGRAM



TRUTH TABLE

COMPARING INPUTS				CASCADING INPUTS			OUTPUTS		
				A>B	A<B	A=B	A>B	A<B	A=B
A3>B3	X	X	X	X	X	X	H	L	L
A3=B3	A2>B2	X	X	X	X	X	H	L	L
A3=B3	A2=B2	A1>B1	X	X	X	X	H	L	L
A3=B3	A2=B2	A1=B1	A0>B0	X	X	X	H	L	L
A3=B3	A2=B2	A1=B1	A0=B0	L	L	L	H	H	L
				X	X	H	L	L	H
				L	H	L	L	H	L
				H	L	L	H	L	L
				H	H	L	L	L	L
A3=B3	A2=B2	A1=B1	A0<B0	X	X	X	L	H	L
A3=B3	A2=B2	A1<B1	X	X	X	X	L	H	L
A3=B3	A2<B2	X	X	X	X	X	L	H	L
A3<B3	X	X	X	X	X	X	L	H	L

X: DONT CARE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
V _I	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _O	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(*) 500 mW: ≅ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

M54/M74HC85

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V_{CC}	Supply Voltage	2 to 6	V	
V_I	Input Voltage	0 to V_{CC}	V	
V_O	Output Voltage	0 to V_{CC}	V	
T_{op}	Operating Temperature: M54HC Series M74HC Series	-55 to +125 -40 to +85	°C °C	
t_r, t_f	Input Rise and Fall Time	$V_{CC} = 2\text{ V}$	0 to 1000	ns
		$V_{CC} = 4.5\text{ V}$	0 to 500	
		$V_{CC} = 6\text{ V}$	0 to 400	

DC SPECIFICATIONS

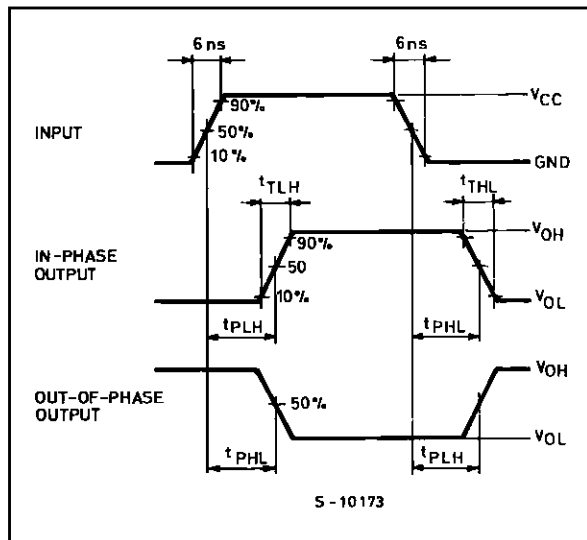
Symbol	Parameter	Test Conditions		Value						Unit			
				$T_A = 25\text{ °C}$ 54HC and 74HC			$-40\text{ to }85\text{ °C}$ 74HC		$-55\text{ to }125\text{ °C}$ 54HC				
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.		
V_{IH}	High Level Input Voltage	2.0			1.5			1.5		1.5		V	
		4.5			3.15			3.15		3.15			
		6.0			4.2			4.2		4.2			
V_{IL}	Low Level Input Voltage	2.0					0.5		0.5		0.5	V	
		4.5					1.35		1.35		1.35		
		6.0					1.8		1.8		1.8		
V_{OH}	High Level Output Voltage	2.0	$V_I = V_{IH}$ or V_{IL}	$I_O = -20\text{ }\mu\text{A}$	1.9	2.0		1.9		1.9		V	
		4.5			4.4	4.5		4.4		4.4			
		6.0			5.9	6.0		5.9		5.9			
		4.5		4.18	4.31		4.13		4.10				
		6.0				$I_O = -5.2\text{ mA}$		5.68		5.8			5.63
V_{OL}	Low Level Output Voltage	2.0	$V_I = V_{IH}$ or V_{IL}	$I_O = 20\text{ }\mu\text{A}$		0.0	0.1		0.1		0.1	V	
		4.5				0.0	0.1		0.1		0.1		
		6.0				0.0	0.1		0.1		0.1		
		4.5		4.0	mA		0.17	0.26		0.33			0.40
		6.0				$I_O = 5.2\text{ mA}$		0.18	0.26		0.33		
I_I	Input Leakage Current	6.0	$V_I = V_{CC}$ or GND			± 0.1		± 1		± 1	μA		
I_{CC}	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND			4		40		80	μA		

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

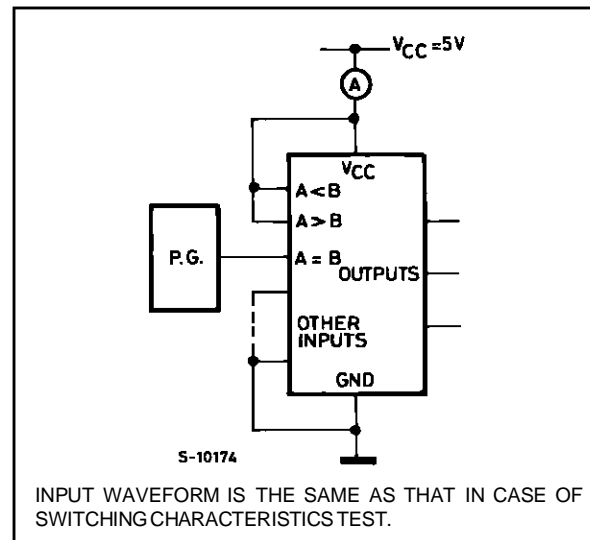
Symbol	Parameter	Test Conditions		Value						Unit	
		V_{CC} (V)		$T_A = 25 \text{ }^\circ\text{C}$ 54HC and 74HC			$-40 \text{ to } 85 \text{ }^\circ\text{C}$ 74HC		$-55 \text{ to } 125 \text{ }^\circ\text{C}$ 54HC		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t_{TLH} t_{THL}	Output Transition Time	2.0			30	75		95		110	ns
		4.5			8	15		19		22	
		6.0			7	13		16		19	
t_{PLH} t_{PHL}	Propagation Delay Time (A, B-OUT)	2.0			96	185		230		280	ns
		4.5			24	37		46		56	
		6.0			20	31		39		48	
t_{PLH} t_{PHL}	Propagation Delay Time (CASCADE-OUT)	2.0			48	95		120		145	ns
		4.5			12	19		24		29	
		6.0			10	16		20		25	
C_{IN}	Input Capacitance				5	10		10		10	pF
$C_{PD} (*)$	Power Dissipation Capacitance				23						pF

(*) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$

SWITCHING CHARACTERISTICS TEST WAVEFORM

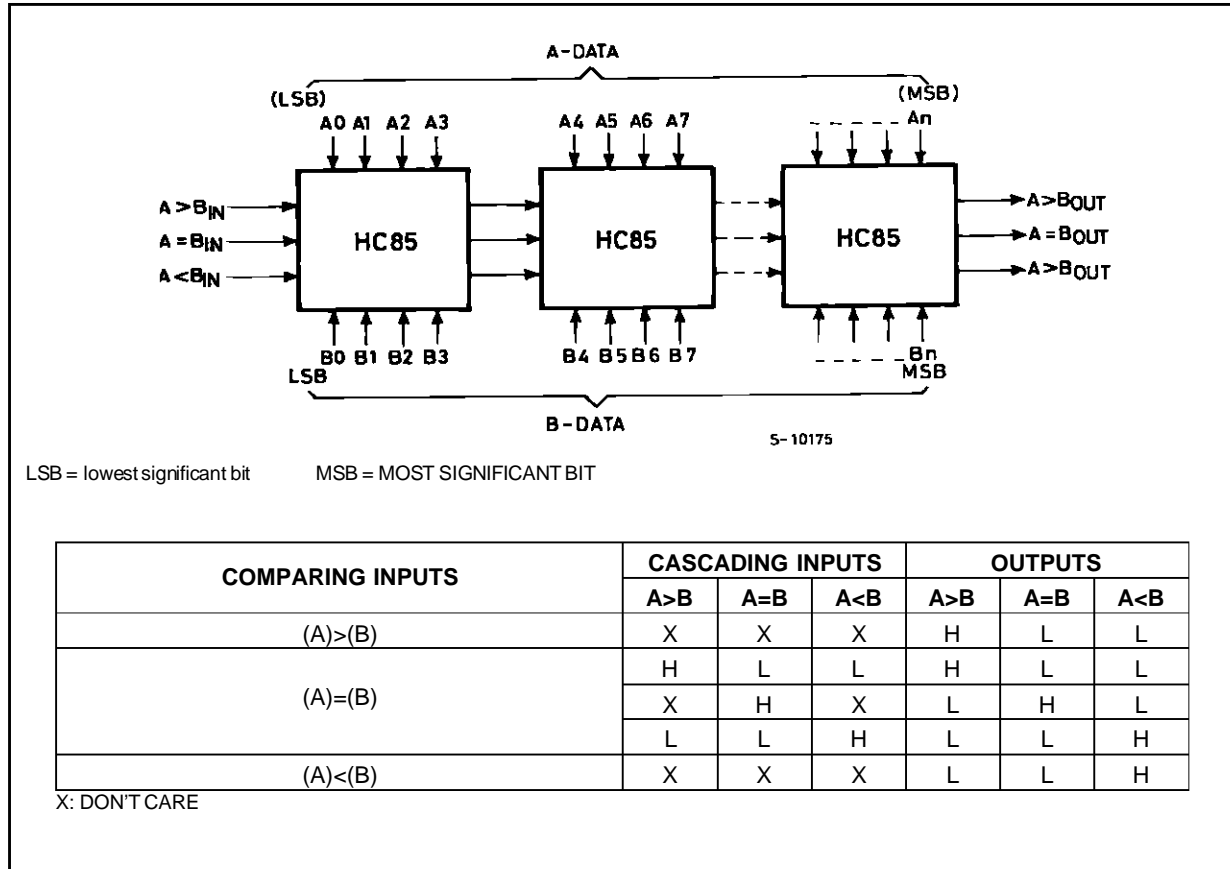


TEST CIRCUIT I_{CC} (Opr.)



INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.

TYPICAL APPLICATION



Plastic DIP16 (0.25) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



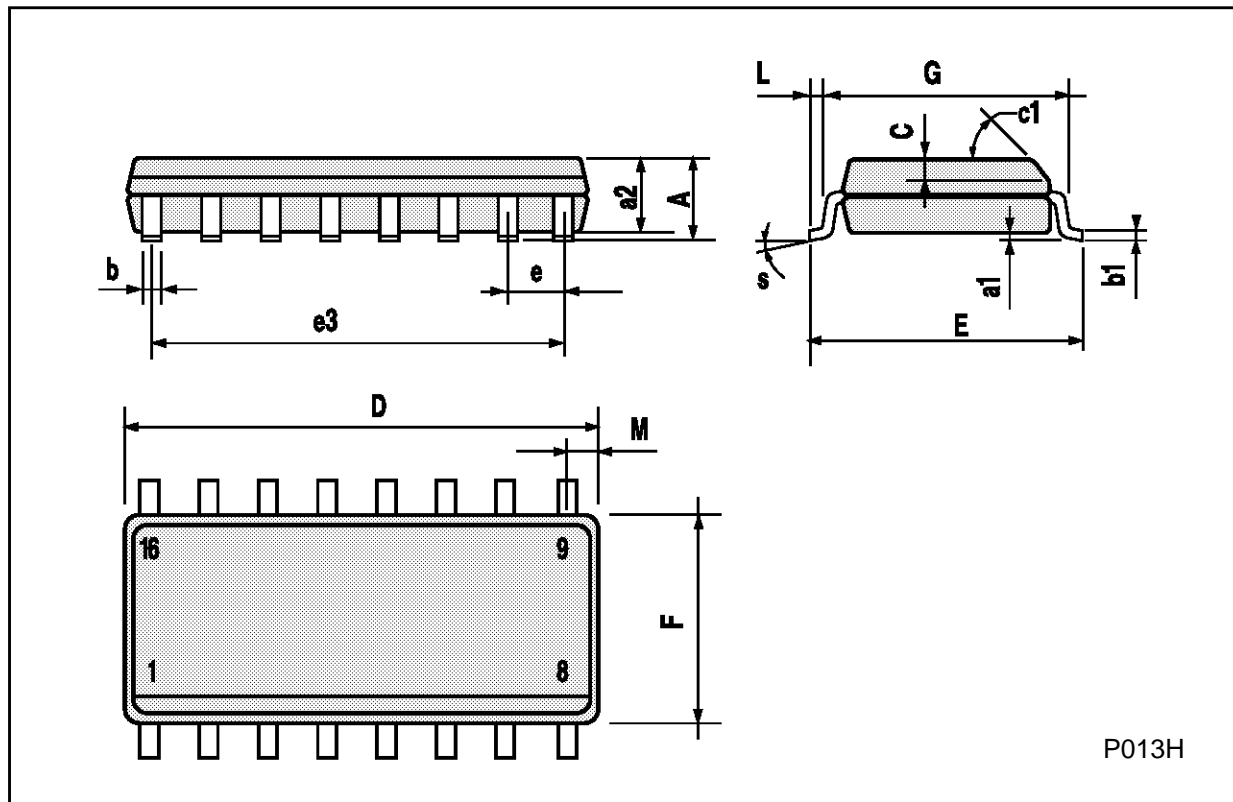
Ceramic DIP16/1 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



SO16 (Narrow) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



P013H

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands -
Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A